

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP097/ NVLS-2906 Applicant: Wu et al. Filing Date March 23, 2004	Application No.: 10/807,680 Group <del>2812</del> 1792
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### U.S. Patent Documents

Examiner Initial	No.	Publication/ Patent No.	Date	Patentee	Class	Sub-class	Filing Date
/MLP/	A1	6,329,017	12/11/01	Liu et al.	X	X	10/04/99
	A2	6,383,466	5/7/02	Domansky et al.			12/28/98
	A3	6,365,266	4/2/02	MacDougall et al.			03/03/00
	A4	5,504,042	4/2/96	Cho et al.			06/23/94
	A5	5,858,457	1/12/96	Brinker et al.			09/25/97
	A6	6,270,846	8/7/01	Brinker et al.			03/02/00
	A7	6,387,453	5/14/02	Brinker et al.			03/02/00
	A8	6,420,441	10/10/99	Allen et al.			12/10/99
	A9	6,271,273	10/10/00	You et al.			10/10/00
	A10	20040096672	05/20/04	Lukas et al.			11/14/02
/MLP/	A11	6,444,715	09/03/02	Mukherjee, et al.			06/06/00

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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
*11/13/07 /MLP/	A12	Humayun et al., <del>"Method For Forming Porous Films By Porogen Removal Combined With In Situ Surface Modification"</del> , U.S. Application No. 10/404,693, filed March 31, 2003.
*4/24/06	A13	Cho et al., <del>"Method And Apparatus For UV Exposure Of Low Dielectric Constant Materials For Porogen Removal And Improved Mechanical Properties"</del> , U.S. Patent Application No. 10/800,377, filed March 11, 2004
*4/30/07	A14	Bandyopadhyay et al., <del>"Method to Improve Mechanical Strength of Low K Dielectric Film Using Modulated UV Exposure"</del> , U.S. Patent Application No. 10/825,888, filed April 16, 2004
*2/27/06 /MLP/	A15	Tipton et al., <del>"Method Of Porogen Removal From Porous Low K Films Using UV Radiation"</del> , U.S. Patent Application No. 10/672,311, filed September 26, 2003
Examiner /Marianne L. Padgett/		Date Considered 11/16/2007

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\* applications reviewed with respect to other IDSs as indicated by date.



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/MLP/	B1	6,420,441	10/10/99	Allen et al.	X	X	12/10/99
	B2	6,271,273	10/10/00	You et al.			10/10/00
	B3	4,885,262	12/5/89	Ting et al.			03/08/89
	B4	5,686,054	11/11/97	Barthel et al.			05/16/95
	B5	5,851,715	12/22/98	Barthel et al.			06/18/97
	B6	6,140,252	10/31/00	Cho et al.			05/05/98
	B7	6,392,017	5/21/02	Chandrashekar			08/04/00
	B8	6,386,466	5/14/02	Ozawa et al.			04/11/00
	B9	4,357,451	11/2/82	McDaniel			08/28/01
	B10	6,479,374	11/12/02	Ioka et al.			09/27/00
	B11	6,548,113	4/15/03	Birnbaum et al.			11/09/00
	B12	20020034626	03/21/02	Liu, et al.			04/18/01
/MLP/	B13	20020001973	01/03/02	Wu, et al.			04/24/01

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/MLP/	B15	Yung et al., "Spin-on Mesoporous Silica Films with Ultralow Dielectric Constants, Ordered Pore Structures, and Hydrophobic Surfaces," Adv. Mater. 2001, 13, No. 14, 1099-1102 July 18
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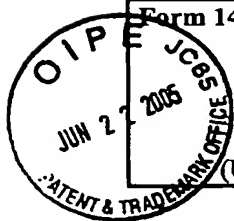
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*7/25/07	/MLP/	C1	Schulberg et al., " <del>System for Deposition of Mesoporous Materials,</del> " U.S. Patent Application No. 10/295,965, filed November 15, 2002, <del>64</del> Pages
		C2	Watkins et al., " <del>Mesoporous Materials and Methods,</del> " U.S. Patent Application No.10/301,013, filed November 21, 2002, <del>34</del> Pages
		C3	Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002 ? event or lecture?
	/MLP/	C4	Justin F. Gaynor, " <del>In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments,</del> " U.S. Patent Application No.10/056,926 filed January 24, 2002, <del>34</del> Pages abandon
Examiner		/Marianne L. Padgett/	Date Considered 11/16/2007

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++ "HMDS/Supercritical Carbon Dioxide Treatment of Plasma Damaged Nanoporous Low k Films"



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	A2	5,789,027	08.04.98	Watkins et al.			
	A3	6,391,932 B1	05.21.02	Gore et al.			
	A4	5,700,844	12.23.97	Hedrick et al.			
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	A6	2002/0123240 A1	09.05.02	Gallagher et al.			
	A7	6,340,628	01.22.02	Van Cleemput, et al.			
	A8	6,383,955	05.07.02	Matsuki, et al.			
	A9	6,596,654	07.22.03	Bayman, et al.			
	A10	2004/0099952	05.27.04	Goodner et al.			
	A11	2004/0102031	05.27.04	Kloster et al.			
	A12	2004/0185679	09.23.04	Ott et al.			
	A13	6,848,458	02.01.05	Shrinivasan et al.			
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	A16	4,882,008	11.21.89	Garza et al.			
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	A18	6,268,276	07.31.01	Chan et al.			
	A19	6,177,329	01.23.01	Pang			
	A20	5,920,790	07.1999	Wetzel et al.			
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/MLP/	A32	6,756,085	06.29.04	Waldfried et al.			
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/MLP/	A1	6,500,770 B1	12.2002	Cheng et al.			
/MLP/	A2	2002/0192980 A1	12.2002	Hogle et al.			

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation
							Yes No

#### Other Documents

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/MLP/	C1	<del>U.S. Office Action mailed July 13, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].</del>
/MLP/	C2	<del>U.S. Office Action mailed July 27, 2005, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].</del> also cited in 7/25/06 IDS
		both applications cited in the IDS of 2/27/2006
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/Marianne L. Padgett/	11/16/2007	

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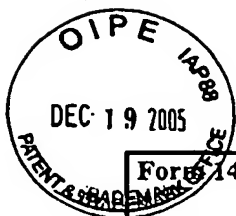
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/MLP/	C2	<del>U.S. Office Action mailed September 1, 2005, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].</del> abandoned
		both applications are also cited in the IDS of 11/13/2006
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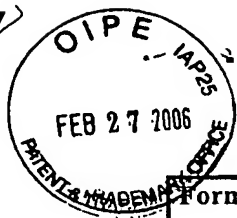
#### Foreign Patent or Published Foreign Patent Application

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							Yes	No

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C1	Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 ( <del>Atty Dkt. NOVLP145/NVLS-3106</del> )
Examiner	/Marianne L. Padgett/	
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/MLP/	A1	6,797,643 B2	09.2004	Rocha-Alvarez et al.	X	X	
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	A3	6,914,014 B2	07.2005	Li et al.			
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	A6	6,610,362 B1	08.2003	Towle, Steven N.			
	A7	6,632,478 B2	10.2003	Gaillard et al.			
	A8	2004/0096593 A1	05.2004	Lukas et al.			
	A9	2004/0161532 A1	08.2004	Kloster et al.			
	A10	2004/0170760 A1	09.2004	Meagley et al.			
	A11	2005/0064698 A1	03.2005	Chang et al.			
	A12	6,715,498 B1	04.2004	Humayun et al.			
/MLP/	A13	5,849,640	12.1998	Hsia et al.			

**Foreign Patent or Published Foreign Patent Application**

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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C1	<del>U.S. Office Action mailed December 27, 2005, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919]. applications cited in 7/23/07 IDS</del>
	C2	<del>U.S. Office Action mailed December 23, 2005, from U.S. Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-002907].</del>
	C3	<del>U.S. Office Action mailed February 7, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821]. abandoned &amp; cited 11/13/06 IDS</del>
	C4	<del>U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].</del>
	C5	<del>U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867]. applications cited in 7/25/06 IDS</del>
/MLP/	C6	<del>U.S. Office Action mailed January 9, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].</del>
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/MLP/	A1	6,573,030 B1	06.03.03	Fairbairn et al.	X	X	
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C1	Subramonium et al., <del>"Pulsed PECVD Method for Modulating Hydrogen Content in Hard Mask"</del> , U.S. Application No. 11/318,269, filed December 23, 2005 (Atty Dkt: NOVLP144/NVLS 3102)
/MLP/	C2	<del>U.S. Office Action mailed February 28, 2006, from U.S. Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS 794]</del> application cited in 11/13/06
/MLP/	C3	<del>U.S. Office Action mailed March 29, 2006, from U.S. Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS 002886]</del>
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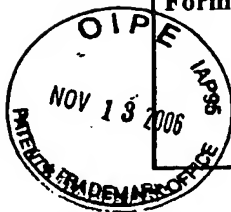
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	A5	2002/0016085	02.2002	Huang et al.			
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	A7	7,018,918	03.2006	Kloster et al.			
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/MLP/	C1	<del>U.S. Office Action mailed May 31, 2006, from U.S. Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932], application also cited 7/23/07 IDS</del>
	C2	<del>U.S. Office Action mailed May 30, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]</del>
	C3	<del>U.S. Office Action mailed May 31, 2006, from U.S. Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867]</del>
	C4	<del>U.S. Office Action mailed May 2, 2006, from U.S. Application No. 11/050,621 [Atty Dkt No. NOVLP100/NVLS-2956]</del>
	C5	<del>U.S. Office Action mailed June 13, 2006, from U.S. Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-2907], application cited in 7/23/07 IDS</del>
	C6	Kelman et al., "Method for Reducing Stress in Porous Dielectric Films", U.S. Application No. 11/369,311, filed March 6, 2006 ( <del>Atty Dkt. NOVLP154/NVLS-3131</del> )
	C7	<del>U.S. Office Action mailed June 28, 2006, from U.S. Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882], application cited in 4/30/07 IDS</del>
/MLP/	C8	<del>U.S. Office Action mailed May 2, 2006, from U.S. Application No. 10/295,965.</del>
	C9	<del>U.S. Office Action mailed August 9, 2005, from U.S. Application No. 10/295,965.</del>
/MLP/	C10	<del>U.S. Office Action mailed June 14, 2006, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919], application also cited in 7/23/07 IDS</del>
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	A2	6,306,564	10.2001	Mullee, William H.			
	A3	2003/0066544 A1	04.2003	Jur et al.			
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	A8	7,087,271 B2	08.2006	Rhee et al.			
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/MLP/	A10	6,331,480	12.2001	Tsai et al.			

**Other Documents**

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/MLP/	C1	<del>U.S. Office Action mailed September 8, 2006, from U.S. Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS 794]</del>
	C2	<del>U.S. Office Action mailed September 7, 2006, from U.S. Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS 2889]</del> application also cited 7/23/07 IDS
	C3	<del>U.S. Office Action mailed July 12, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS 2821]</del> abandon
	C4	<del>Wu et al., "Methods for Fabricating High Hardness/Modules Low Dielectric Constant Materials," Novellus Systems, Inc., Appln No. 11/369,658, filed March 6, 2006, pp. 1-35. [NOVLP148/NVLS 3111]</del>
/MLP/	C5	<del>Dhas et al., "Method of Reducing Defects in PECVD TEOS Films," Novellus Systems, Inc., Appln No. 11/396,303, filed March 30, 2006, pp. 1-21. [NOVLP160/NVLS 3168]</del>
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C1	<del>U.S. Office Action mailed December 27, 2006, from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].</del>
	C2	<del>Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant Materials for Poregen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 11/656,661, filed January 22, 2007, pages 1-28. [Atty Docket No. NOVLP089D1/NVLS-2887D1]</del>
	C3	<del>Shrinivasan et al., "Single-Chamber Sequential Curing of Semiconductor Wafers," Novellus Systems, Inc., Application No. 11/115,576, filed April 26, 2005, pages 1-29. [NOVLP127/NVLS-3044]</del>
	C4	<del>Kamian et al., "Ultra Violet Light Treatment Lead Look for Dielectric Films," Novellus Systems, Inc., Application No. 11/561,834, filed November 20, 2006, pages 1-25. [NOVLP184/NVLS-3109]</del>
	C5	<del>Schravendijk et al., "UV Treatment of Etch Stop and Hard Mask Films for Selectivity and Hermeticity Enhancement," Novellus Systems, Inc., Application No. 11/696,102, filed April 3, 2007, pages 1-22. [NOVLP191/NVLS-3218]</del>
	C6	<del>Vancouver et al., "PECVD Methods for Producing Ultra Low-K Dielectric Films Using UV Treatment," Application No. 11/608,056, filed December 7, 2006, pages 1-34. [NOVLP196/NVLS-3238] application also cited in 7/23/07 IDS</del>
	C7	<del>Tarafdar et al., "Sequential Deposition/Anneal Film Densification Method", Novellus Systems, Inc., filed September 11, 2006, Application No. 11/519,445, pages 1-37. [Atty Dckt. NOVLP116X1/NVLS-2975C1]</del>
/MLP/	C8	<del>Schravendijk, "UV Treatment of FSG Films to Improve Film Stability," Novellus Systems, Inc., Application No. 11/622,423, filed January 11, 2007, pages 1-31. [NOVLP189/NVLS-3215]</del>
Examiner	/Marianne L. Padgett/	
Date Considered	11/16/2007	

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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	NOVLP097/NVLS-2906
	Application No.:	10/807,680
	Applicant	Wu et al.
	Filing Date	March 23, 2004
	Group	<del>2812</del> 1792
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Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
/MLP/	1.	2003/0224156	12.2003	Kirner et al.			
	2.	2003/0111263	06.2003	Fornof et al.			
	3.	2002/0132496	09.2002	Ball et al.			
	4.	6,662,631	12.2003	Baklanov et al.			
	5.	2006/0145305	07.2006	Boyanov et al.			
	6.	7,098,149	08.2006	Lukas et al.			
	7.	2006/0040507	02.2006	Mak et al.			
	8.	2005/0230834	10.2005	Schmitt et al.			
	9.	2006/0105566	05.2006	Waldfried et al.			
	10.	2004/0018717	01.2004	Fornof et al.			
	11.	2004/0213911	10.2004	Misawa et al.			
	12.	2004/0249006	12.2004	Gleason et al.			
	13.	2005/0095840	05.2005	Bhanap et al.			
	14.	2006/0178006	08.2006	Xu et al.			
	15.	6,572,925 B2	06.2003	Zubkov et al.			
	16.	6,566,278 B1	05.2003	Harvey et al.			
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/MLP/	19.	6,365,528 B1	04.2002	Sukharev et al.			

### Foreign Patent or Published Foreign Patent Application

Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation	
							Yes	No
/MLP/	20.	WO 03/052794 A2	26.06.2003	PCT				in English
/MLP/	21.	WO 03/005429 A1	16.01.2003	PCT				in English

### Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
/MLP/	22.	<del>U.S. Office Action mailed November 30, 2006, from</del> U.S. Application No. 10/927,777 [Atty Dkt No. NOVLP106/NVLS-2930].

Examiner	/Marianne L. Padgett/	Date Considered	11/16/2007
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Form 1449 (Modified)

Information Disclosure  
Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No.	NOVLP097/NVLS-2906
Application No.:	10/807,680
Applicant	Wu et al.
Filing Date	March 23, 2004
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	Page 2 of 2

/MLP/	23.	<del>U.S. Office Action mailed March 28, 2007, from U.S. Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889].</del>
/MLP/	24.	<del>U.S. Office Action mailed January 24, 2007, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].</del>
	25.	<del>U.S. Office Action mailed June 21, 2007, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].</del>
/MLP/	26.	<del>U.S. Notice of Allowance and Fee Due mailed December 19, 2006, from U.S. Application No. 10/800,409. [NOVLP098/NVLS-2907].</del>
	27.	<del>U.S. Office Action mailed April 9, 2007, from U.S. Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-2907].</del>
/MLP/	28.	<del>Niu et al., "Methods for Improving the Cracking Resistance of Low-K Dielectric Materials," Novellus Systems, Inc., Appl. No. 11/376,510, filed March 14, 2006, pages 1-28. [NOVLP099D1/NVLS-2896D1].</del>
	29.	<del>U.S. Office Action dated May 22, 2007, from U.S. Application No. 11/376,510 [Atty Dkt. NOVLP099D1/NVLS-2896D1].</del>
	30.	<del>U.S. Notice of Allowance and Fee Due mailed April 9, 2007, from U.S. Application No. 10/927,777. [NOVLP106/NVLS-2930]</del>
	31.	<del>Allowed Claims from U.S. Application No. 10/927,777. [NOVLP106/NVLS-2930]</del>
/MLP/	32.	<del>U.S. Final Office Action mailed April 3, 2007, from U.S. Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932].</del>
/MLP/	33.	<del>U.S. Notice of Allowance and Fee Due mailed December 20, 2006, from U.S. Application No. 10/860,340. [NOVLP099A/NVLS-2896].</del>
/MLP/	34.	<del>Wu et al., "PECVD Methods for Producing Ultra Low-K Dielectric Films Using UV Treatment," Novellus Systems, Inc., Appl. No. 11/608,056, filed December 7, 2006, pages 1-34. [NOVLP196/NVLS-3238].</del>
/MLP/	35.	<del>Wu et al., "Methods for Improving Performance of ODC Films with Dielectric Constant &lt; 4.0," Novellus Systems, Inc., Appl. No. 11/693,661, filed March 29, 2007, pages 1-46. [NOVLP200/NVLS-3269].</del>

Examiner /Marianne L. Padgett/

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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	NOVLP097/ NVLS-2906	10/807,680
	Applicant:	
	Wu et al.	
	Filing Date	Group
	March 23, 2004	<del>2812</del> 1792

**Foreign Patent or Published Foreign Patent Application**

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No
/MLP/	B1	WO95/07543	03.16.95	WIPO			X	
							in English	

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C1	Jan, C.H., et al, 90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology, 2003 IEEE Interconnect Technology Conference. (no month)
*7/23/07	C2	Wu et al., U.S. Application No. 10/789,103 ( <del>Atty Docket No. NOVLP094</del> ), entitled: <del>Methods For Producing Low K CDO Films With Low Residual Stress</del>
*7/23/07	C3	Wu et al., U.S. Application No. 10/820,525 ( <del>Atty Docket No. NOVLP091</del> ), entitled: <del>Methods For Producing Low K CDO Films With Low Residual Stress</del>
*7/23/07	C4	Wu et al., U.S. Application No. 10/800,409 ( <del>Atty Docket No. NOVLP098</del> ), entitled: <del>Methods For Producing Low K CDO Films</del>
/MLP/	C5	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 ( <del>Atty Dkt. NOVLP030</del> )
	C6	<del>U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt. NOVLP028) abandoned 1/9/2004 &amp; no PGPub</del>
/MLP/	C7	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 ( <del>Atty Dkt. NOVLP028X1</del> ) abandoned
*11/13/06	C8	Tipton et al., "Method for Removal of Porogens From Porous Low K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVLP069/NVLS-000821 abandon
*11/13/06	C9	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt. NOVLP064) application
*2/27/06	C10	Tipton et al., "Method Of Porogen Removal From Porous Low K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated September 7, 2004 (Atty Dkt. NOVLP075/NVLS-000820)
	C11	<del>Tipton et al., "Method Of Porogen Removal From Porous Low K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated December 28, 2004 (Atty Dkt. NOVLP075/NVLS-000820)</del>
Examiner /Marianne L. Padgett/		Date Considered 11/16/2007

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*application cited in other IDS submissions of indicated date.

Note office actions are not published & inappropriate for listing, however such citations are being considered citations at the application, but only one citation is needed, thus 'duplicates' on the same IDS are crossed-out.

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	NOVLP097/ NVLS-2906	10/807,680
	Applicant:	
	Wu et al.	
	Filing Date	Group
	March 23, 2004	<del>2012</del> 1792

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	C12	<del>Tipton et al., "Method For Removal Of Porogens From Porous Low K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Any Dkt. NOVLP069). duplicates above application</del>
/MLP/	C13	R.D. Miller et al., "Phase-Separated Inorganic-Organic Hybrids for Microelectronic Applications," MRS Bulletin, October 1997, Pages 44-48
	C14	Jin et al., "Nanoporous Silica as an Ultralow-k Dielectric," MRS Bulletin, October 1997, Pages 39-42
	C15	Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodicity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572
	C16	Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured Al," Journal of the Electrochemical Society, 148 (4) B152-B156 (2001) Pages B152-B156 (no month)
	C17	Holland et al., "Nonlithographic Technique for the Production of Large Area High Density Gridded Field Sources," J. Vac. Sci. Technol. B 17(2), Mar/Apr. 1999, Pages 580-582
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**	C19	Clube et al., "White Paper from Holotronic Technologies SA; downloaded from <a href="http://www.hdotronic.com/whitepaper/fine-patt.pdf">www.hdotronic.com/whitepaper/fine-patt.pdf</a> on March 12, 2002
	C20	Meli et al., "Self-Assembled Masks for the Transfer of Nanometer-Scale Patterns into Surfaces: Characterization by AFM and LFM", Nano Letters, Vol. 2, No. 2, 2002, 131-135 ; published on web 12/29/2001 (no month)
	C21	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003. Electronic News, online
	C22	Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), <del>56</del> (2003). November, pages 56-58 & 60
	C23	Van Bavel et al., Future Fab International, 16, (2004). February 3 ***
	C24	Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003.(no month) IEEE, p.242-244, Journal unknown
	C25	Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International. copy incomplete-right side all pages
	C26	Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003.(no month) cut off
/MLP/	C27	Bhadri N. Varadarajan, "Tensile Silicon Nitride - P1264 NESL", C & F Study, August 21, 2003. ?Publisher unclear? Novellus confidential
		BV-WW30/03 ?
Examiner	/Marianne L. Padgett/	
	Date Considered	11/16/2007

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*\* "Fine-Pattern Lithography for Large Substrates Using a Holographicmask-Aligner (revised edition)"

\*\*\* "Efficient Pore Sealing Crucial for Future Interconnects"



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	NOVLP097/ NVLS-2906	10/807,680
	Applicant:	
	Wu et al.	
	Filing Date	Group
	March 23, 2004	<del>2812</del> 1792

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C28	Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20, 2004, pages 1-24. [Atty Docket No. NOVLP108/ NVLS 2933].
/MLP/	C29	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt. NOVLP099)
	C30	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Office Action dated March 2, 2005, (Atty Dkt. NOVLP099)
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		C35 Fox et al., "Methods For Producing Low-Stress Carbon-Doped Oxide Films With Improved Integration Properties", U.S. Application No. 10/987,208, filed November 12, 2004 (Atty Dkt. NOVLP104)
*7/25/06		C36 Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt. NOVLP100)
		C37 Draeger et al., "Creation Of Porosity In Low-K Films By Photo-Disassociation Of Imbedded Nanoparticles," U.S. Application No. 11/146,456, filed June 6, 2005 (Atty Dkt. NOVLP100X1)
*7/23/07		C38 Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 10/927,777, filed August 27, 2004 (Atty Dkt. NOVLP106)
*7/23/07	/MLP/	C39 Wu et al., "Methods For Improving Integration Performance Of Low Stress CDO Films", U.S. Application No. 10/941,502, filed September 14, 2004 (Atty Dkt. NOVLP107)
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/Marianne L. Padgett/		11/16/2007

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	Applicant: Wu et al. Filing Date March 23, 2004	Group <del>2812</del> 1792

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/MLP/	C40	<del>Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115)</del>
Examiner	/Marianne L. Padgett/	Date Considered 11/16/2007

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